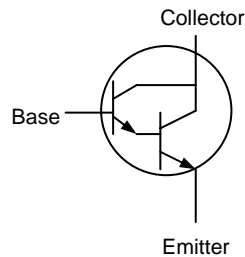
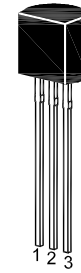


## NPN Silicon Darlington Transistor



## BC517



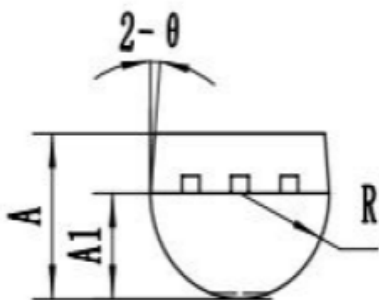
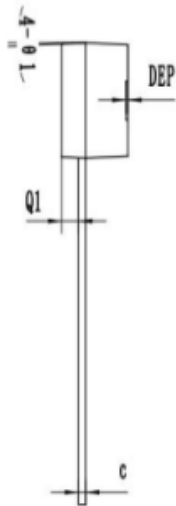
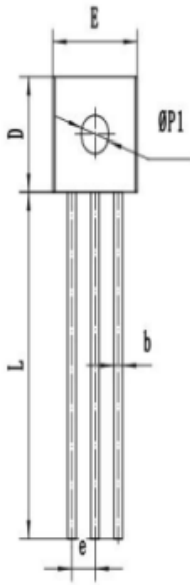
1. Collector 2. Base 3. Emitter  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	40	V
Collector Emitter Voltage	$V_{CES}$	30	V
Emitter Base Voltage	$V_{EBO}$	10	V
Collector Current	$I_C$	500	mA
Total Power Dissipation	$P_{tot}$	625	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$ , $I_C = 20\text{ mA}$	$h_{FE}$	30,000	-	-	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	$I_{CBO}$	-	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 30\text{ V}$	$I_{CES}$	-	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 10\text{ V}$	$I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CES}$	30	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	10	-	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$ , $I_B = 0.1\text{ mA}$	$V_{CE(sat)}$	-	-	1	V
Base Emitter On Voltage at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$	$V_{BE(on)}$	-	-	1.4	V
Current Gain Bandwidth Product at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	-	200	-	MHz



SYMBOL	MM		
	MIN	NOM	MAX
*A	3.00	3.25	3.50
A1	2.20	2.30	2.40
*b	0.40	0.45	0.50
*c	0.25	0.30	0.35
*D	4.50	4.60	4.70
*E	4.50	4.60	4.70
*e	1.22	1.27	1.32
*L	14.00	14.30	14.60
R	2.20	2.30	2.40
Q1	0.85	0.90	0.95
θ	3°	5°	7°
Ø1	1°	3°	5°
ØP1	1.40	1.50	1.60
DEP	0.05	0.10	0.20
带*为检验尺寸			